

isc N-Channel MOSFET Transistor

IRFP048N, IIRFP048N

FEATURES

- Static drain-source on-resistance: R_Ds(on)≤16mΩ
- Enhancement mode:
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

- Ultra Low On-resistance
- Fast Switching

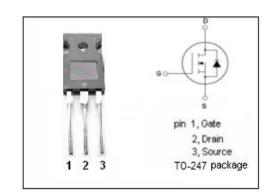


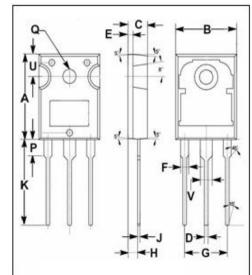
• ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage	55	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous	64	А
I _{DM}	Drain Current-Single Pulsed	210	А
P _D	Total Dissipation @T _C =25°C	140	W
Tj	Max. Operating Junction Temperature	175	°C
T _{stg}	Storage Temperature	-55~175	$^{\circ}$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(j-c)	Channel-to-case thermal resistance	1.1	°C/ W
Rth(j-a)	Channel-to-ambient thermal resistance	40	°C/W





	mm		
DIM	MIN	MAX	
Α	19.80	20.20	
В	15.40	15.80	
C	4.90	5.10	
D	0.90	1.10	
E	1.40	1.60	
F	1.90	2.10	
G	10.80	11.00	
Н	2.40	2.60	
J	0.50	0.70	
K	19.50	20.50	
P	3.90	4.10	
Q	3.30	3.50	
U	5.20	5.40	
V	2.90	3.10	



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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =250 μ A	55			V
V _{GS(th)}	Gate Threshold Voltage	VDS=VGS; I _D =250 μ A	2.0		4.0	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =37A			16	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±20V			±0.1	μ A
I _{DSS}	Drain-Source Leakage Current	V _{DS} =55V; V _{GS} = 0V			25	μ А
V _{SD}	Diode forward voltage	I _S =37A, V _{GS} = 0V			1.3	V

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